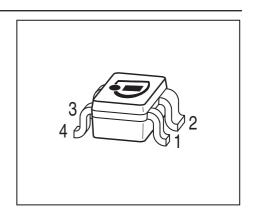


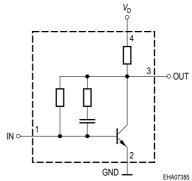
Si-MMIC-Amplifier in SIEGET® 25-Technologie

- Cascadable 50 Ω-gain block
- Unconditionally stable
- Gain $|S_{21}|^2 = 13$ dB at 1.8 GHz $IP_{3out} = +13$ dBm at 1.8 GHz $(V_D = 3 \text{ V}, I_D = \text{typ. 6.7 mA})$
- Noise figure NF = 2.2 dB at 1.8 GHz
- Reverse isolation > 28 dB and return loss IN / OUT > 12 dB at 1.8 GHz
- Pb-free (RoHS compliant) package



Circuit Diagram





ESD (Electrostatic discharge) sensitive device, observe handling precaution!

Туре	Marking	Pin Configuration			Package	
BGA420	BLs	1, IN	2, GND	3, OUT	4, VD	SOT343

Maximum Ratings

Parameter	Symbol	Value	Unit
Device current	I _D	15	mA
Device voltage	V_{D}	6	V
Total power dissipation	P _{tot}	90	mW
<i>T</i> _S = 110 °C			
RF input power	P_{RFin}	0	dBm
Junction temperature	$T_{\rm j}$	150	°C
Ambient temperature	T _A	-65 1 50	
Storage temperature	T _{stg}	-65 150	

Thermal Resistance

Junction - soldering point ¹⁾	R _{thJS}	≤ 410	K/W
--	-------------------	-------	-----

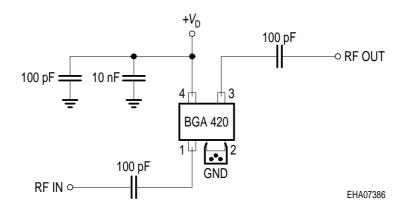
 $^{^{1}}$ For calculation of R_{thJA} please refer to Application Note Thermal Resistance



Electrical Characteristics at T_A = 25 °C, unless otherwise specified.

Parameter	Symbol		Unit		
		min.	typ.	max.	
AC characteristics $V_D = 3 V$, $Z_0 = 50 \Omega$	•	•		•	•
Device current	I _D	5.4	6.7	8	mA
Insertion power gain	$ S_{21} ^2$				dB
f = 0.1 GHz		17	19	-	
f = 1 GHz		15	17	-	
f = 1.8 GHz		11	13	-	
Reverse isolation	S12	25	28	-	
<i>f</i> = 1.8 GHz					
Noise figure	NF				
f = 0.1 GHz		_	1.9	2.3	
f = 1 GHz		_	2.2	2.6	
f = 1.8 GHz		_	2.3	2.7	
Intercept point at the output	IP _{3out}	10	13	-	dBm
<i>f</i> = 1 GHz					
1dB compression point	P _{-1dB}	-6	-2.5	-	
<i>f</i> = 1 GHz					
Return loss input	<i>RL</i> _{in}	8	11	-	dB
<i>f</i> = 1.8 GHz					
Return loss output	<i>RL</i> _{out}	12	16	-	
<i>f</i> = 1.8 GHz					

Typical biasing configuration



Note: 1) Large-value capacitors should be connected from pin 4 to ground right at the device to provide a low impedance path.

2) The use of plated through holes right at pin 2 is essential for pc-board-applications. Thin boards are recommended to minimize the parasitic inductance to ground.

2

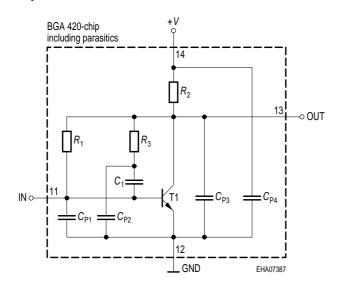
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Typical S-Parameters at T_A = 25 °C

f	S ₁₁		S ₂₁			S ₁₂		S ₂₂	
GHz	MAG	ANG	MAG	ANG	MAG	ANG	MAG	ANG	
V _D = 3	$V_{\rm D}$ = 3 V, $Z_{\rm O}$ = 50 Ω								
0.1	0.5686	-8.5	9.314	170.6	0.0268	12.7	0.2808	-8.6	
0.5	0.5066	-19.2	8.393	149.4	0.0248	11.7	0.2613	-3.8	
8.0	0.4404	-28.7	7.352	135.2	0.0236	25.6	0.2361	-6.7	
1	0.3904	-34.6	6.69	126.8	0.024	35.9	0.2144	-9	
1.5	0.2841	-50.5	5.244	111.1	0.0314	57.2	0.1398	-15	
1.8	0.2343	-60.6	4.567	104	0.0378	63.5	0.0979	-18.2	
1.9	0.2136	-64.1	4.355	102	0.0406	66.1	0.0838	-21.5	
2	0.2062	-68.4	4.165	99.7	0.0426	67.2	0.0689	-22.2	
2.4	0.1688	-89.7	3.417	91.7	0.0549	71.4	0.0224	-48	
3	0.1558	-104.9	2.861	85.3	0.0682	73.1	0.0284	-147.5	

Spice-model BGA 420



T1	T501
R ₁	14.5kΩ
R_2	140Ω
R_3	2.4kΩ
C ₁	2.3pF
C _{P1}	0.2pF
C _{P2}	0.2pF
C _{P2}	0.6pF
C _{P4}	0.1pF

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3



Transistor Chip Data T1 (Berkley-SPICE 2G.6 Syntax) :

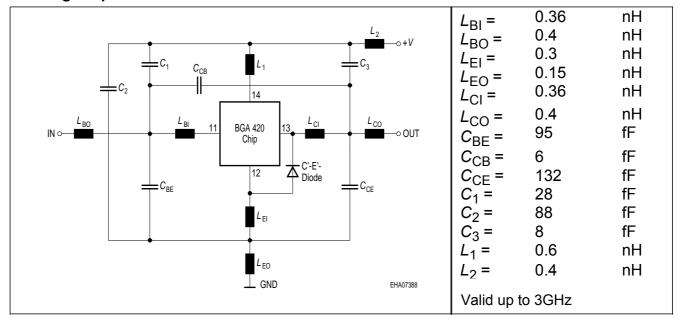
IS =	0.21024	fA	BF =	83.23	-	NF =	1.0405	-
VAF =	39.251	V	IKF =	0.16493	Α	ISE =	15.761	fA
NE =	1.7763	-	BR =	10.526	-	NR =	0.96647	-
VAR =	34.368	V	IKR =	0.25052	Α	ISC =	0.037223	fA
NC =	1.3152	-	RB =	15	Ω	IRB =	0.21215	Α
RBM =	1.3491	Ω	RE =	1.9289		RC =	0.12691	Ω
CJE =	3.7265	fF	VJE =	0.70367	V	MJE =	0.37747	-
TF =	4.5899	ps	XTF =	0.3641	-	VTF =	0.19762	V
ITF =	1.3364	mA	PTF =	0	deg	CJC =	96.941	fF
VJC =	0.99532	V	MJC =	0.48652	-	XCJC =	0.08161	-
TR =	1.4935	ns	CJS =	0	fF	VJS =	0.75	V
MJS =	0	-	XTB =	0	-	EG =	1.11	eV
XTI =	3	-	FC =	0.99469	-	TNOM	300	K

C'-E'-Diode Data (Berkley-SPICE 2G.6 Syntax) :

IS = 2 fA N = 1.02 - RS =	20 Ω
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All parameters are ready to use, no scaling is necessary

Package Equivalent Circuit:



Extracted on behalf of Infineon Technologies AG by: Institut für Mobil-und Satellitentechnik (IMST)

For examples and ready to use parameters please contact your local Infineon Technologies distributor or sales office to obtain a Infineon Technologies CD-ROM or see Internet: http://www.infineon.com/silicondiscretes

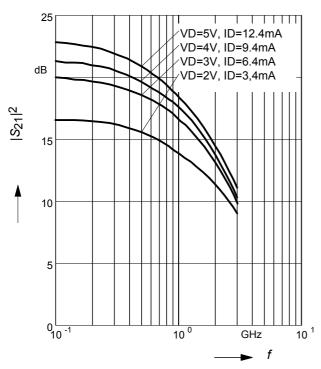
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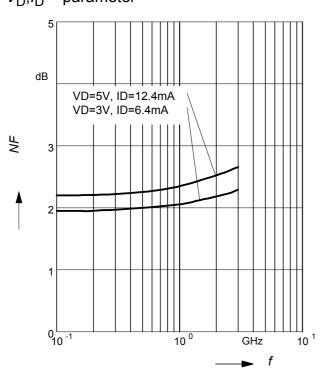
Insertion power gain $|S_{21}|^2 = f(f)$

$V_{\rm D}$, $I_{\rm D}$ = parameter



Noise figure NF = f(f)

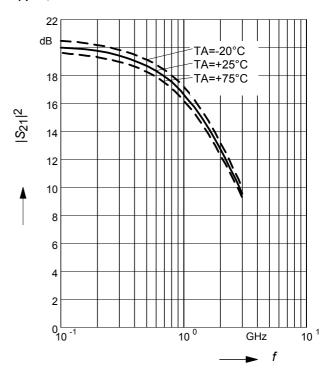
$V_{\rm D}$, $I_{\rm D}$ = parameter



Insertion power gain $|S_{21}|^2 = f(f)$

$$V_{\rm D} = 3 \, {\rm V}$$

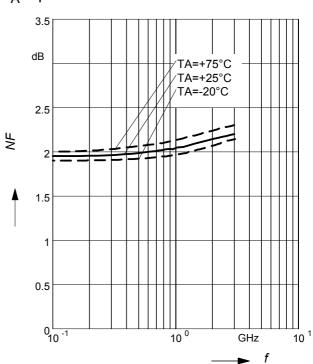
 T_A = parameter



Noise figure NF = f(f)

$$V_{\rm D} = 3V$$

 T_A = parameter

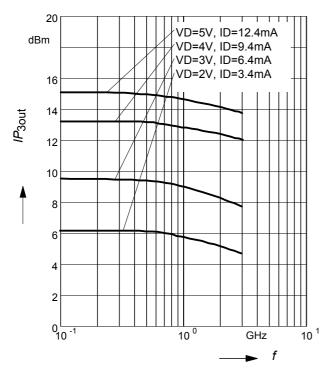




Intercept point at the output

$$IP_{3out} = f(f)$$

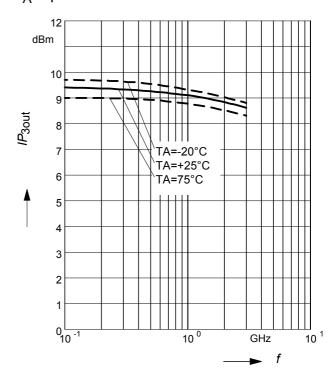
 $V_{\rm D}$, $I_{\rm D}$ = parameter



Intercept point at the output

$$IP_{3out} = f(f), V_{D} = 3V$$

 T_A = parameter

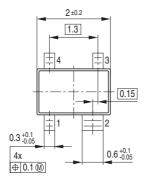


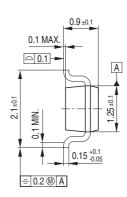
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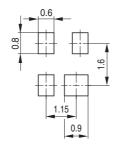
Package Outline



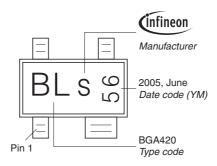




Foot Print

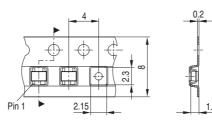


Marking Layout (Example)



Standard Packing

Reel ø180 mm = 3.000 Pieces/Reel Reel ø330 mm = 10.000 Pieces/Reel





Edition 2009-11-16

Published by Infineon Technologies AG 81726 Munich, Germany

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